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(54) Title: GENERATING A NON-REVERSIBLE STATE AT A BITCELL HAVING A FIRST MAGNETIC TUNNEL JUNCTION AND A SECOND MAGNETIC TUNNEL JUNCTION

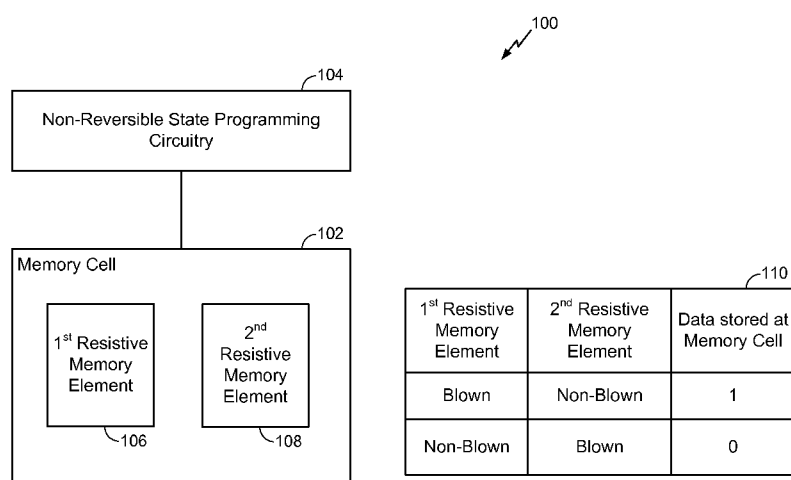


FIG. 1

(57) Abstract: A method of generating a non-reversible state at a bitcell having a first magnetic tunnel junction (MTJ) and a second MTJ includes applying a program voltage to the first MTJ of the bitcell without applying the program voltage to the second MTJ of the bitcell. A memory device includes a bitcell having a first MTJ and a second MTJ and programming circuitry configured to generate a non-reversible state at the bitcell by applying a program signal to a selected one of the first MTJ and the second MTJ of the bitcell.



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